

Docket No.: 60188-555

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yoshinao HARADA

Serial No.: Divisional of Appln.

Serial No. 10/122,366

Group Art Unit: Not yet assigned

Filed: June 25, 2003

Examiner: Not yet assigned

For: SEMICONDUCTOR DEVICE AND METHOD FOR PRODUCING THE SAME

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 10/122,366, filed April 16, 2002, which is relied upon for an earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION				ATTY. DOCKET NO. 60188-555		SERIAL NO. Divisional of Appln. Serial No. 10/122,366	
(PTO-1449)				APPLICANT Yoshinao HARADA			
				FILING DATE June 25, 2003		GROUP Not yet assigned	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 6,013,553	01/2000	WALLACE et al.			
		US 6,521,911 B2	2/2003	PARSONS et al.			
		US 2002/0043666 A1	4/2002	PARSONS et al.			
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		EP 0143700 A2	6/1985	BAUDRANT et al.			
		EP 0077200 A2	4/1980	KATO et al.			
		WO 02/09167 A3	1/2002	PARSONS			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		CHAMBERS and PARSONS, "Yttrium silicate formation on silicon: Effect of silicon preoxidation and nitridation on interface reaction kinetics" Applied Physics Letters 77(15), 9 October 2000, pp. 2385-2387					
		GURVITCH et al., "Study of thermally oxidized yttrium films on silicon" Applied Physics Letter 51(12), 21 September 1987, pp. 919-921					
		KALKUR et al., "Yttrium oxide based metal-insulator-semiconductor structures on silicon" Thin Solid Films 170, 1989, pp. 185-189.					
		PIERSON, HUGH, O., Handbook of Chemical Vapor Deposition, Noyes Publications, Park Ridge, New Jersey pp. 229-230.					
EXAMINER		DATE CONSIDERED					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.